

## Supplementary Materials for

### **Dynamic polaronic screening for anomalous exciton spin relaxation in two-dimensional lead halide perovskites**

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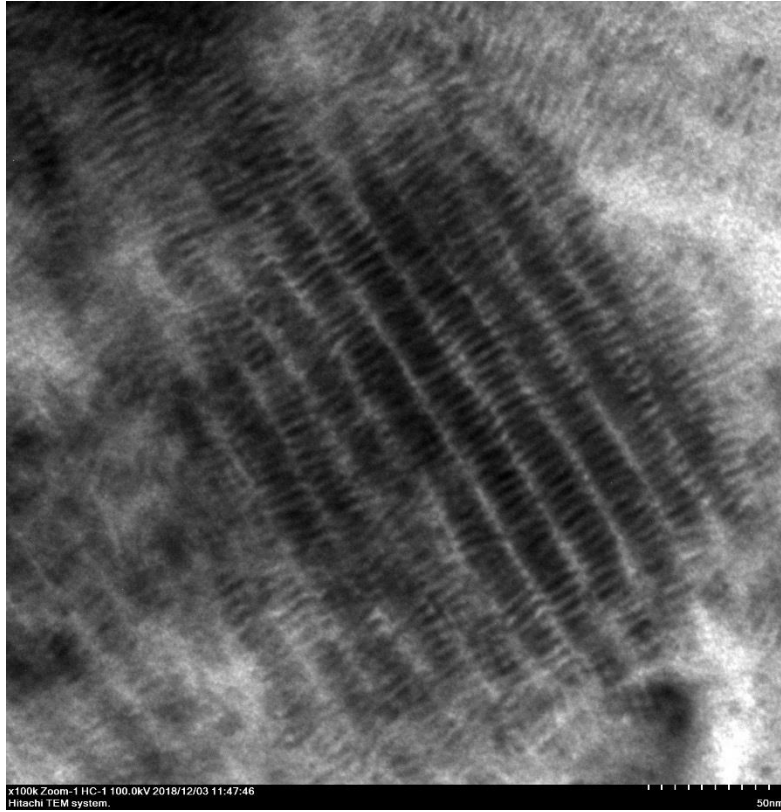
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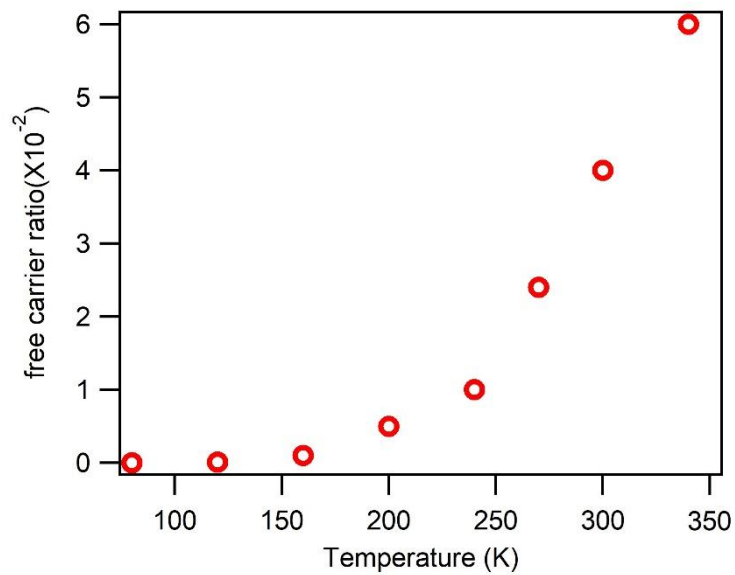
Figs. S1 to S8

Notes S1 to S5

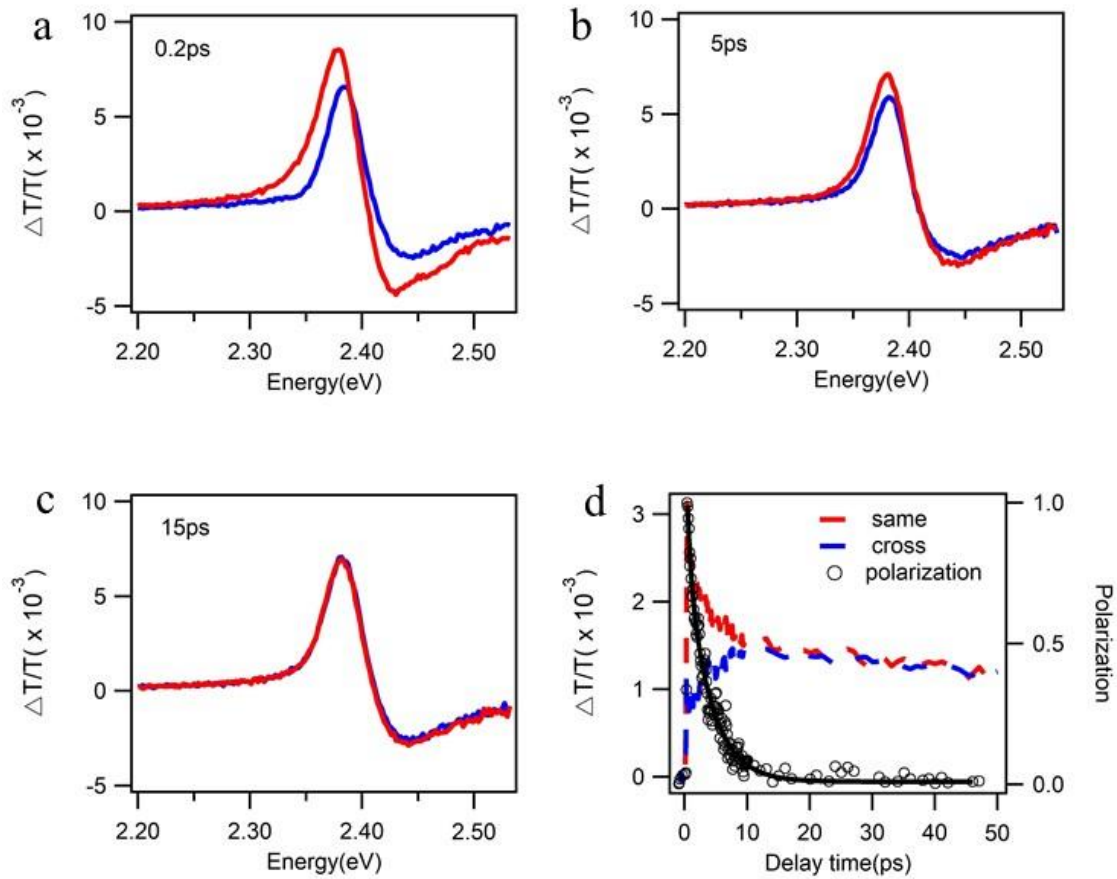
References



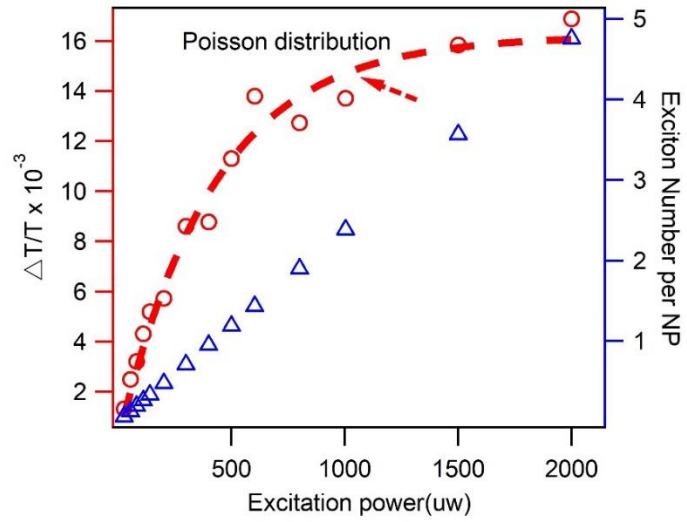
**Figure S1.** TEM image of the synthesized NPs which are self-assembly on copper grid in a face-to-face manner.



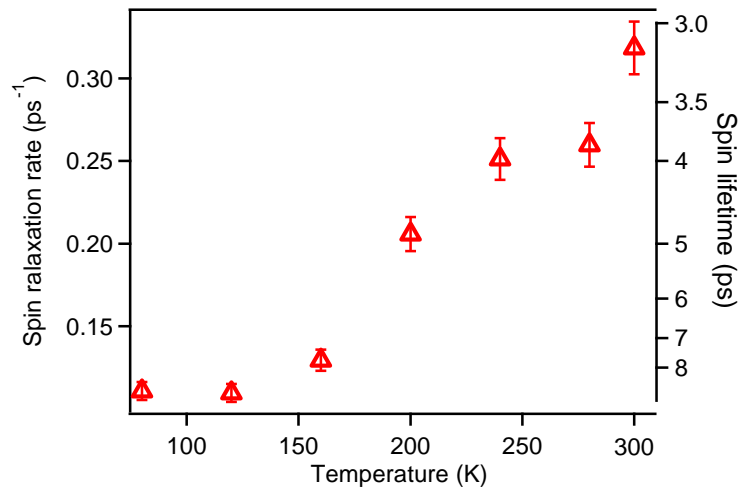
**Figure S2.** Estimated free carrier ratio at different lattice temperature based on Saha-Langmuir equation



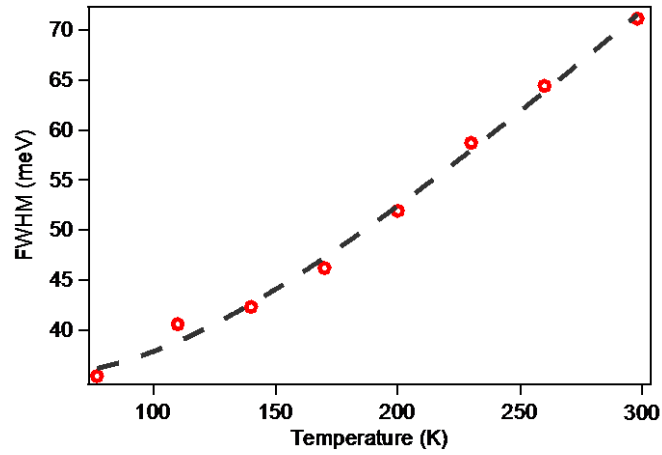
**Figure S3.** Spin Depolarization process in 3D CsPbBr<sub>3</sub> bulk film. (a-c) Spectral evolution for same and opposite pump-probe configuration at different pump-probe time delay (0.2 ps, 5 ps, 15 ps, respectively). (d) TA dynamics for same and opposite pump-probe configurations averaged at 2.34-2.39 eV. Also plotted is calculated valley polarization kinetics and its single exponential fit.



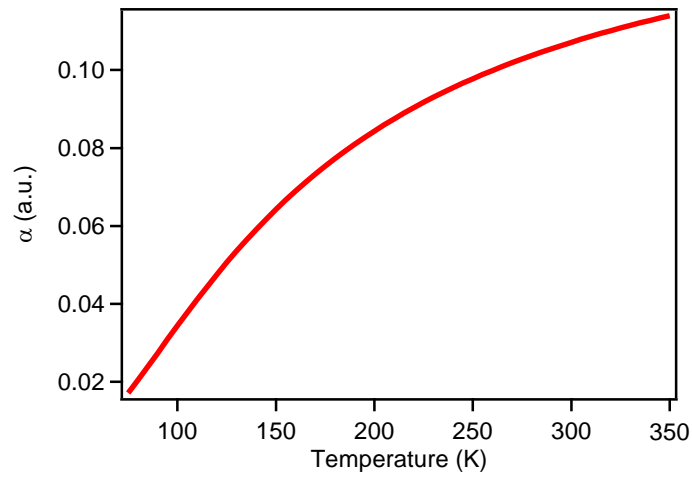
**Figure S4.** Estimated average exciton number per NP under different excitation power based on Poisson distribution and saturation curve.



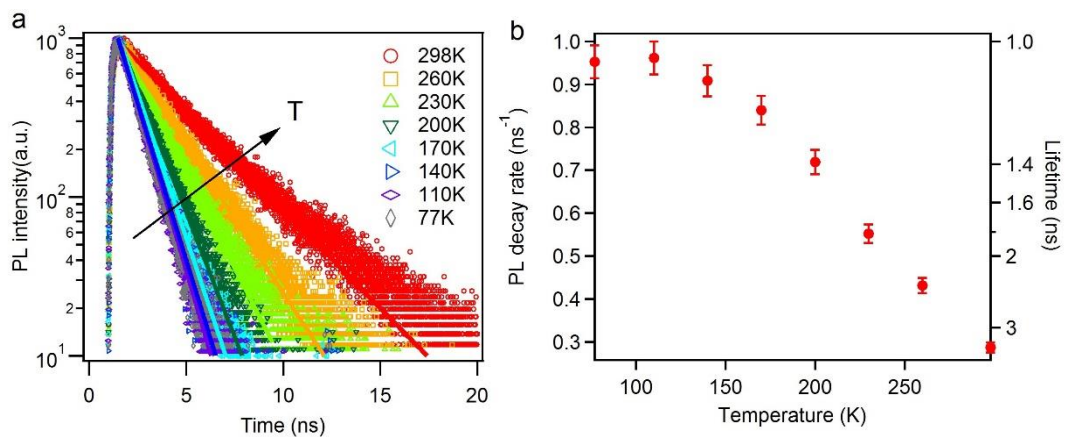
**Figure S5.** Spin relaxation rate as a function of temperature for 3D CsPbBr<sub>3</sub> film which shows a faster spin flip with temperature.



**Figure S6.** PL linewidth (FWHM) of 3L CsPbBr<sub>3</sub> NPs as a function of temperature. The data points can be well described with the phenomenological model shown in main text with  $\Gamma_0 = 35$  meV,  $A = 79$  meV and  $E_{ph} = 25$  meV.



**Figure S7.** The dependence of polaronic coupling constant  $\alpha$  on temperature.  $\alpha$  increases quickly with increasing temperature in CsPbBr<sub>3</sub>.



**Figure S8.** PL decay as a function of temperature. (a) PL decay kinetics and (b) lifetime as a function of temperature for 3L CsPbBr<sub>3</sub> NPs, showing a longer lifetime with increasing temperature.

### Note S1. Estimate exciton dissociation ratio based on Saha–Langmuir equation

According to Saha-Langmuir equation, the fraction of free carrier over the total density of excitation for a 2D semiconductor,  $x$ , can be expressed as(47)

$$\frac{x^2}{1-x} = \frac{1}{n} \frac{\mu}{\pi \hbar^2} kT e^{\frac{-E_b}{kT}} \quad (S1)$$

where  $\mu$  is exciton reduced mass which is approximated to  $0.15 m_e$ ,  $E_b$  is the exciton binding energy which is 180 meV for 3L CsPbBr<sub>3</sub>. The excitation density is approximated to be an exciton per NPs, which is  $10^{12}$  per cm<sup>2</sup>. The temperature dependent exciton dissociation ratio can be estimated according to equation S1 and the results are present in Fig. S2. Obviously, bound exciton is the dominant (> 95%) species in the investigated temperature range.

### Note S2. Excitation energy dependent initial polarization based on MSS mechanism.

According to MSS mechanism, the electron-hole exchange interaction acts as a fluctuating effect magnetic field and facilitates spin precession and the exciton spin depolarization rate can be expressed as(14)

$$k_s \approx \langle \Omega_K^2 \rangle \tau_p \quad (S2)$$

where  $\langle \Omega_K^2 \rangle$  is the square of magnetic field averaged over exciton states which is proportional to the exciton center momentum  $K^2$ ,  $\tau_p$  is exciton scattering time which can be approximated to be constant at a certain temperature. Thus, we get a square relation between the exciton spin depolarization rate and exciton center momentum.

$$k_s \propto K^2$$

Within effective mass approximation, the exciton energy and exciton center momentum obey parabolic dispersion relation, which can be expressed as

$$K = \frac{\sqrt{2\mu\varepsilon_{pump}}}{\hbar} \quad (S3)$$

where  $\varepsilon_{pump}$  is the excess energy of the pump pulse relative to the exciton resonance. Combining these relationships, we get a linear dependence of  $k_s$  on excess excitation energy.

### **Note S3. Estimate exciton density under different excitation power**

According to Poisson distribution, the probability of generating  $N$  exciton per NP is given by  $P_N = \frac{\langle N \rangle^N}{N!} e^{-\langle N \rangle}$  and the probability of generating not less than one exciton per NP can be expressed as

$$P_{N \geq 1} = 1 - P_0 = 1 - e^{-\langle N \rangle} \quad (\text{S4})$$

$$\langle N \rangle = \sigma \cdot F \quad (\text{S5})$$

Where  $\langle N \rangle$  is the average exciton number per NP and is proportional to the absorption section  $\sigma$  and excitation energy.

The probability of generating not less than one exciton per NP,  $P_{N \geq 1}$  can be estimated by the ground state bleach signal magnitude when the Auger recombination process completed. By fitting the bleach signal magnitude with excitation power with Poisson distribution equation, the average exciton number per NP under certain excitation power can be figured out and the result is given in Supplementary Figure 4. Together with NP lateral size, the excitation density can also be derived. We note the exciton density is averaged value.

### **Note S4. Another two common carrier spin relaxation mechanisms and their temperature dependence**

In Maialle-Silva-Sham (MSS) mechanism, electron-hole exchange interaction flips the exciton spin as a whole.<sup>(14)</sup> In principle, exciton spin can be relaxed via the successive flip of either kind of carrier (electron or hole). There are two common mechanisms that can trigger carrier spin flipping process<sup>(48)</sup>: Elliott-Yafet (EY) and Dyakonov-Perel (DP) mechanisms. In excitonic systems, these two mechanisms lead to much slow spin flip process compared to MSS mechanism as can be inferred by orders of magnitude faster exciton spin relaxation rate than single electron/hole in TMDC and perovskites.

In Elliott-Yafet (EY) mechanism, the effective magnetic field is produced by spin-orbit interaction, which mixes wavefunctions with opposite spins. Both the electrical field produced by lattice vibrations or charged impurities can be transformed to an



effective magnetic field. Spin rotates during the collisions and the spin relaxation rate is proportional to the momentum scattering rate.

$$k_s = \chi^2 \tau_p^{-1} \quad (\text{S6})$$

where  $\chi$  is the spin mixing factor and  $\tau_p^{-1}$  is the momentum scattering rate. In nondegenerate semiconductors,  $k_s \approx T^2 \tau_p^{-1}$ . (48)  $\tau_p^{-1}$  increases with T due to phonon scattering contribution. Therefore EY mechanism would predict a faster spin relaxation rate when increasing T and has been involved to account for the thermally accelerated spin relaxation rate observed in TMDs heterostructures. EY mechanism is usually very weak in semiconductors with large bandgap.

In bulk semiconductor without central symmetry, D'yakonov-Perel' (DP) mechanism could play an important in spin relaxation process. There, the band spin degeneracy is lifted, creating an effective magnetic field and causing the spin procession. Different from EY mechanism, the spin rotates not during but between collisions. The carrier spin relaxation in 2D system can be express as (49)

$$k_s \approx \alpha T \tau_p \quad (\text{S7})$$

where  $\alpha$  is a coefficient of spin splitting,  $\tau_p$  is the momentum scattering. Assuming T independent  $\alpha$ , the T effect for DP mechanism looks very similar to MSS mechanism, except the effective magnetic field from different origins. Therefore, DP mechanism should also yield an increasing of carrier spin relaxation rate at higher temperature, as predicted by MSS mechanism.

For perovskites with centrosymmetric structure, in principle,  $\alpha$  should be negligible and DP spin relaxation channel should be closed. But local thermal fluctuation can create dynamic symmetry breaking and Rashba effect in perovskite. (5) Higher temperature assists spin splitting thus larger  $\alpha$ , activating DP spin relaxation channel. (46) Considering the additional T effect on  $\alpha$ , higher T and Rashba effect should lead to faster spin relaxation, which is opposite to experimental results.

#### **Note S5. Temperature dependent polaron coupling constant in perovskites**

The strength of electron-phonon coupling in ionic crystal can be described by Fröhlich polaron coupling constant  $\alpha$ , which is given by

$$\alpha \equiv \frac{e^2}{\hbar} \frac{1}{4\pi\epsilon} \left( \frac{1}{\epsilon_\infty} - \frac{1}{\epsilon_0} \right) \sqrt{\frac{m}{2\hbar\omega}} \quad (\text{S7})$$

Where  $e$  is the electron charge;  $\epsilon$  is the dielectric constant of vacuum;  $\epsilon_\infty$  and  $\epsilon_0$  high frequency and low frequency dielectric constants, respectively;  $\omega$  is the angular frequency of the LO phonon mode. so  $\alpha$  is proportional to dielectric response factor  $1/\bar{\epsilon} = 1/\epsilon_\infty - 1/\epsilon_0$ .

Both  $\epsilon_\infty$  and  $\epsilon_0$  in 3D bulk CsPbBr<sub>3</sub> has been established. (37) The effective dielectric constant values in 2D CsPbBr<sub>3</sub> could be different. Here, we simply take the values from 3D CsPbBr<sub>3</sub> to show a general temperature effect since the main physical picture remains same.  $\epsilon_\infty$  is 4 in CsPbBr<sub>3</sub> and  $\epsilon_0$  is temperature dependent due to thermally activated lattice vibration

$$\epsilon_0 = \epsilon_\infty + \frac{A}{\exp\left(\frac{E_a}{kT}\right) - 1} \quad (\text{S8})$$

where prefactor  $A = 6.5$ ,  $E_a = 20$  meV. (37)

The prefactor  $A$  in perovskite is nearly 4-5 orders of magnitude larger than conventional inorganic semiconductors due to large anharmonicity. (37) Therefore,  $\epsilon_0$  shows strong dependence on temperature, which has to be considered. Since  $\epsilon_0$  increases with temperature, the polaron coupling constant  $\alpha$  also increase with the temperature monotonically, as shown in Fig. S7.

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